

MOSFET – Small Signal, N-Channel, Single

60 V, 340 mA, SC-70

2N7002W, 2V7002W

Features

- ESD Protected
- Low R_{DS(on)}
- Small Footprint Surface Mount Package
- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Rating	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	60	V	
Gate-to-Source Voltage	V_{GS}	±20	V	
	Ι _D	310 220	mA	
t < 5 s		340 240		
Power Dissipation (Note 1) Steady State t < 5 s	P _D	280 330	mW	
Pulsed Drain Current (t _p = 10 μs)	I _{DM}	1.4	Α	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	ç	
Source Current (Body Diode)	I _S	250	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

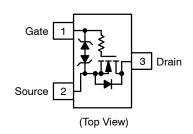
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	450	°C/W
Junction-to-Ambient - t ≤ 5 s (Note 1)	$R_{\theta JA}$	375	

Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX (Note 1)
60 V	1.6 Ω @ 10 V	340 mA
	2.5 Ω @ 4.5 V	

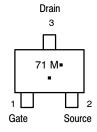
SIMPLIFIED SCHEMATIC





SC-70/SOT-323 CASE 419 STYLE 8

MARKING DIAGRAM & PIN ASSIGNMENT



71 = Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel
2V7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test	Condition	Min	Тур	Max	Units
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			-	71	-	mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V,	T _J = 25°C	-	-	1.0	μΑ
		V _{DS} = 60 V	T _J = 150°C	-	-	15	μΑ
		V _{GS} = 0 V,	T _J = 25°C	_	-	100	nA
		V _{DS} = 50 V	T _J = 150°C	_	-	10	μА
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS}	= ±20 V	-	-	±10	μΑ
		V _{DS} = 0 V, V _{GS}	= ±10 V	-	-	450	nA
		V _{DS} = 0 V, V _{GS}	= ±5.0 V	_	-	150	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 250 \mu A$		1.0	-	2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-	4.0	-	mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$ $V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$		-	1.19	1.6	Ω
				-	1.33	2.5	
Forward Transconductance	9FS	V _{DS} = 5 V, I _D = 200 mA		-	530	-	mS
CHARGES AND CAPACITANCES				-			
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz,		_	24.5	-	pF
Output Capacitance	C _{OSS}	V _{DS} = 20 V	V _{DS} = 20 V		4.2	-	1
Reverse Transfer Capacitance	C _{RSS}	1		-	2.2	-	1
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _E	os = 10 V;	-	0.7	-	nC
Threshold Gate Charge	Q _{G(TH)}	$I_D = 200 \text{ mA}$		-	0.1	-	
Gate-to-Source Charge	Q_{GS}	1		-	0.3	-	
Gate-to-Drain Charge	Q_{GD}	1		-	0.1	-	1
SWITCHING CHARACTERISTICS, V _{GS}	= V (Note 3)	•		•			
Turn-On Delay Time	t _{d(ON)}	$V_{GS} = 10 \text{ V}, V_{DD} = 25 \text{ V},$ $I_{D} = 500 \text{ mA}, R_{G} = 25 \Omega$		_	12.2	-	ns
Rise Time	t _r			-	9.0	-	
Turn-Off Delay Time	t _{d(OFF)}			-	55.8	-	
Fall Time	t _f			-	29	_	1
DRAIN-SOURCE DIODE CHARACTER	ISTICS			-			
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V,	T _J = 25°C	_	0.8	1.2	V
		$I_S = 200 \text{ mA}$ $T_J = 85^{\circ}\text{C}$		_	0.7	-	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 µs, duty cycle ≤ 2%

3. Switching characteristics are independent of operating junction temperatures

2N7002W, 2V7002W

TYPICAL CHARACTERISTICS

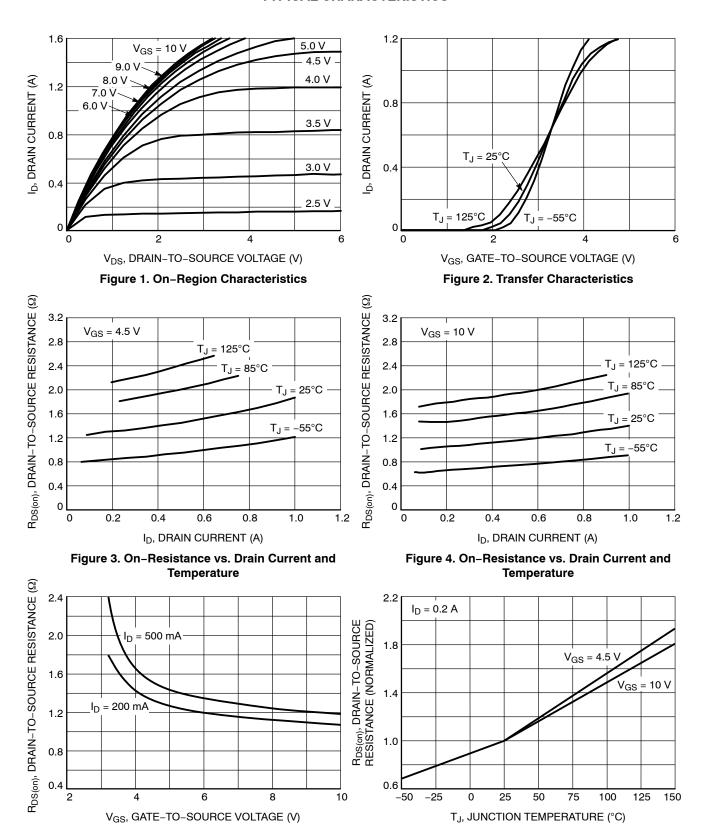


Figure 5. On-Resistance vs. Gate-to-Source Voltage

Figure 6. On–Resistance Variation with Temperature

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TYPICAL CHARACTERISTICS

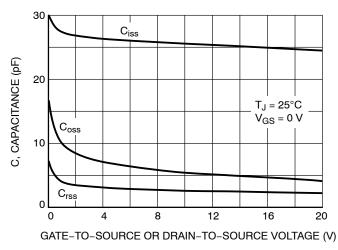


Figure 7. Capacitance Variation

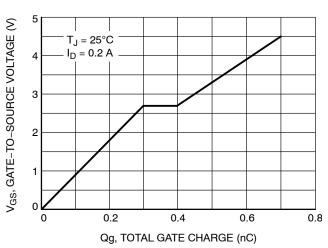


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

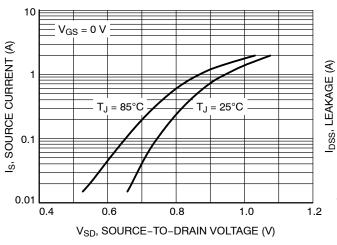


Figure 9. Diode Forward Voltage vs. Current

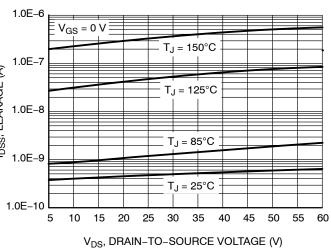


Figure 10. Drain-to-Source Leakage Current vs. Voltage





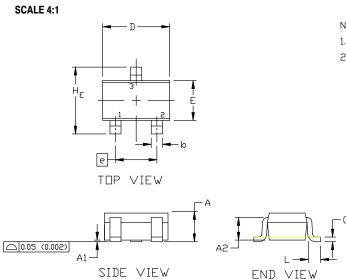
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DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS INCHES					
	М.	ILLIMETE	.K2	INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



GENERIC MARKING DIAGRAM

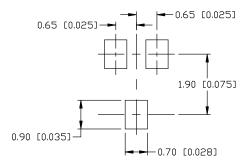


XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER	STYLE 7: PIN 1. BASE	STYLE 8: PIN 1. GATE	STYLE 9: PIN 1. ANODE	STYLE 10: PIN 1. CATHODE	STYLE 11: PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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